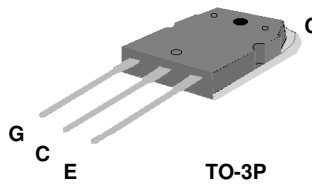


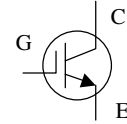


N-Channel Insulated Gate Bipolar Power Transistor

High Speed Switching
 Low Saturation Voltage
 Typical $V_{CE(sat)} = 3.0V$ at $I_C=30A$
 Industry-standard TO-3P
 RoHS-compliant, halogen-free



V_{CES}	1000V
I_C	30A



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	1000	V
V_{GE}	Gate-Emitter Voltage	± 30	V
I_C at $T_C=25^\circ C$	Collector Current	6	A
I_C at $T_C=100^\circ C$	Collector Current	30	A
I_{CM}	Pulsed Collector Current	120	A
P_D at $T_C=25^\circ C$	Maximum Power Dissipation	208	W
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8 inch from case for 5 seconds .	300	$^\circ C$

Notes:

1. Repetitive rating: Pulse width limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-Case	0.6	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-Ambient	40	$^\circ C/W$

Electrical Specifications at $T_J=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collect-to-Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	1000	-	-	V
I_{GES}	Gate-to-Emitter Leakage Current	$V_{GE}=\pm 30V, V_{CE}=0V$	-	-	± 500	nA
I_{CES}	Collector-Emitter Leakage Current	$V_{CE}=1000V, V_{GE}=0V$	-	-	1	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=30A$	-	3	3.6	V
		$V_{GE}=15V, I_C=60A$	-	3.8	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=1mA$	3	4.4	7	V
Q_g	Total Gate Charge	$I_C=30A$	-	55	88	nC
Q_{ge}	Gate-Emitter Charge	$V_{CC}=500V$	-	12	-	nC
Q_{gc}	Gate-Collector Charge	$V_{GE}=15V$	-	27	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=500V,$ $I_C=30A,$	-	3	0	-ns
t_r	Rise Time	$V_{GE}=15V,$ $R_G=5\Omega,$	-	4	0	-ns
$t_{d(off)}$	Turn-off Delay Time	Inductive Load	-	105	-	ns
t_f	Fall Time		-	290	440	ns
E_{on}	Turn-On Switching Loss		-	1.2	-	mJ
E_{off}	Turn-Off Switching Loss		-	1.7	-	mJ
C_{ies}	Input Capacitance	$V_{GE}=0V$	-	1320	2110	pF
C_{oes}	Output Capacitance	$V_{CE}=30V$	-	105	-	pF
C_{res}	Reverse Transfer Capacitance	$f=1.0MHz$	-	9	-	pF

Ordering Information

AP30G100W-HF-3TB

RoHS-compliant halogen-free TO-3P, shipped in tubes



Typical Electrical Characteristics

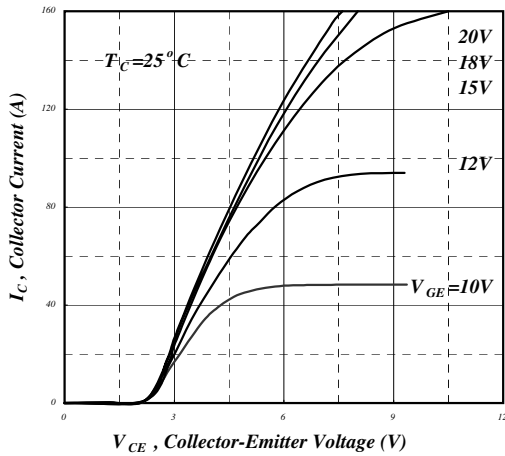


Fig 1. Typical Output Characteristics

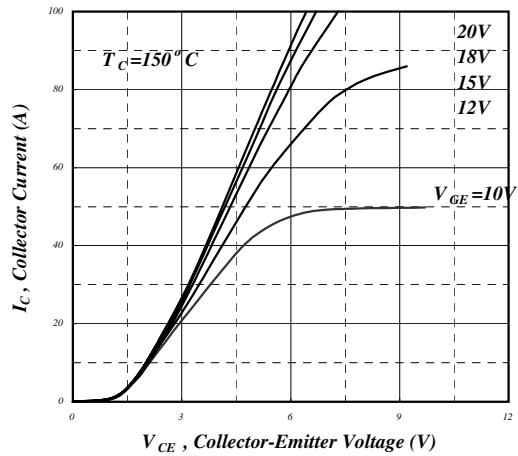


Fig 2. Typical Output Characteristics

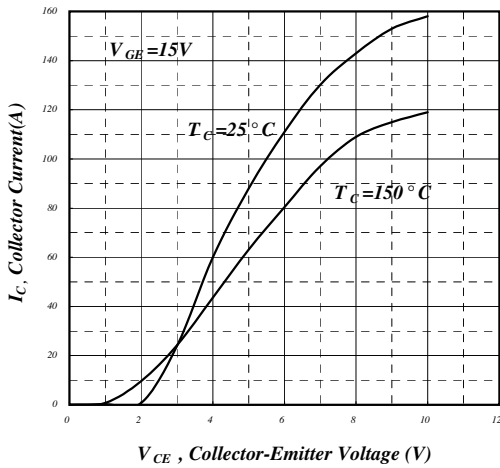


Fig 3. Typical Saturation Voltage Characteristics

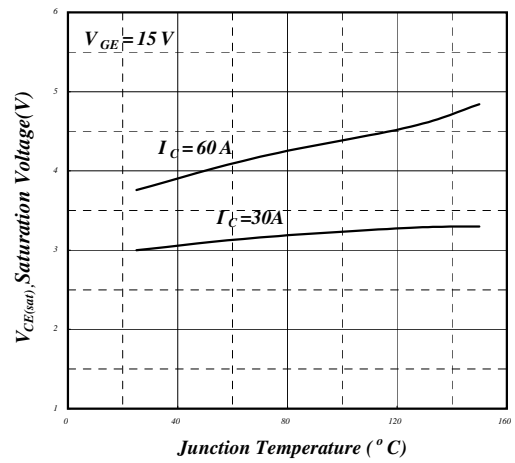


Fig 4. Typical Collector-Emitter Voltage vs. Junction Temperature

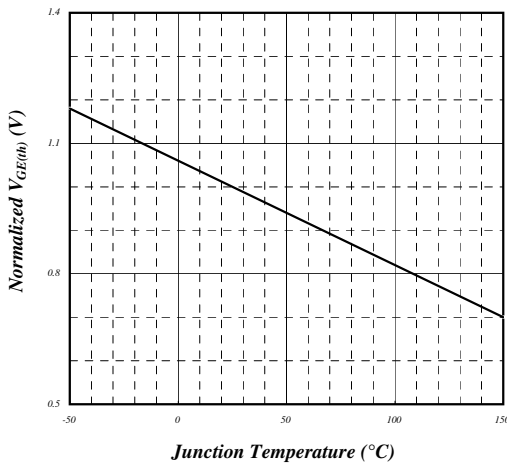


Fig 5. Gate Threshold Voltage vs. Junction Temperature

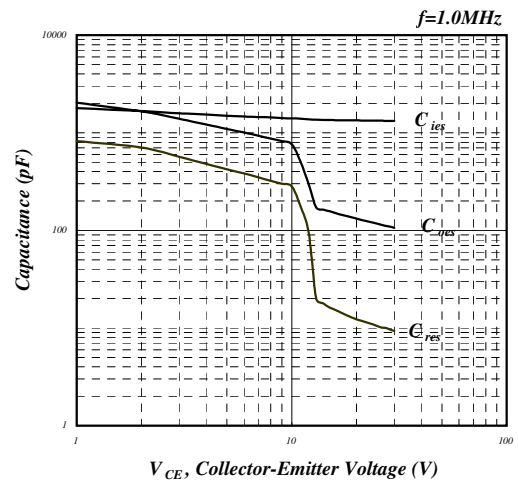


Fig 6. Typical Capacitance Characteristics



Typical Electrical Characteristics (cont.)

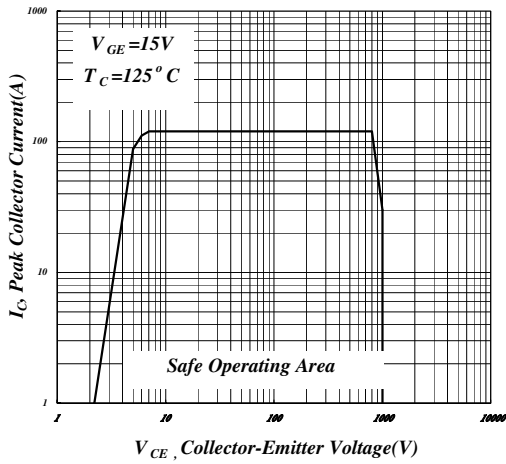


Fig 7. Turn-off SOA

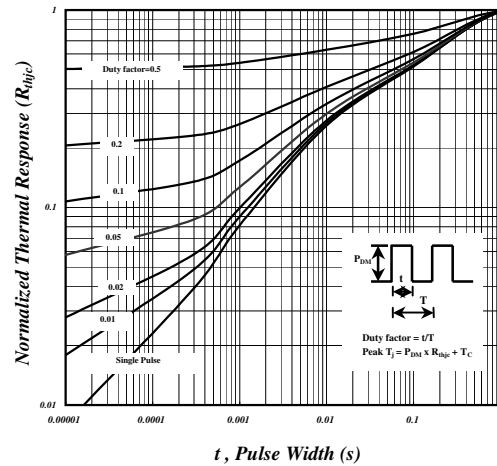


Fig 8. Effective Transient Thermal Impedance

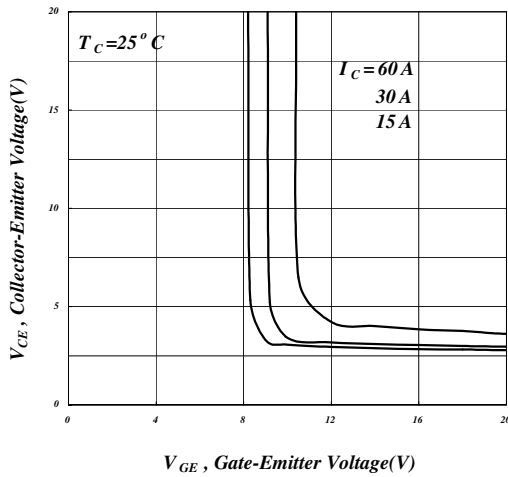


Fig 9. Saturation Voltage vs. V_{GE}

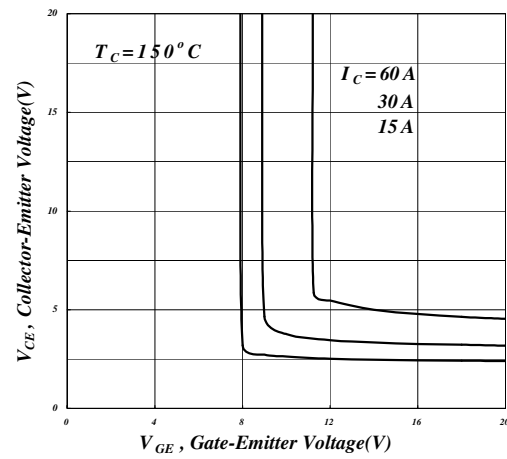


Fig 10. Saturation Voltage vs. V_{GE}

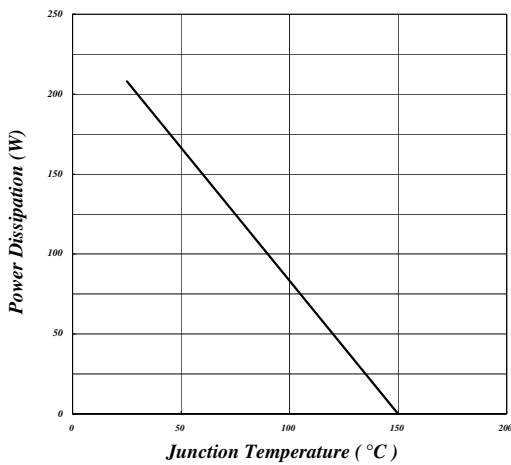


Fig 11. Power Dissipation vs. Junction Temperature

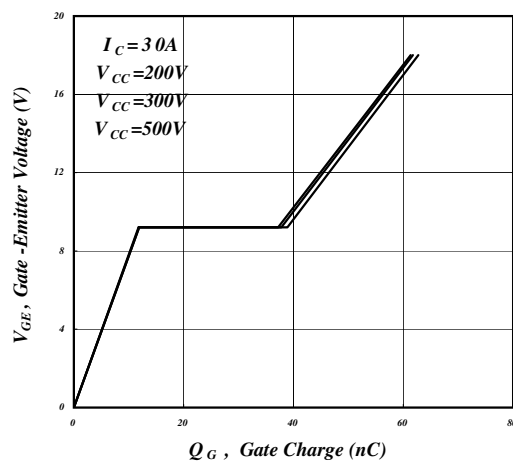
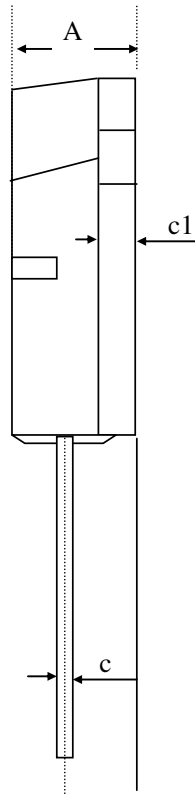
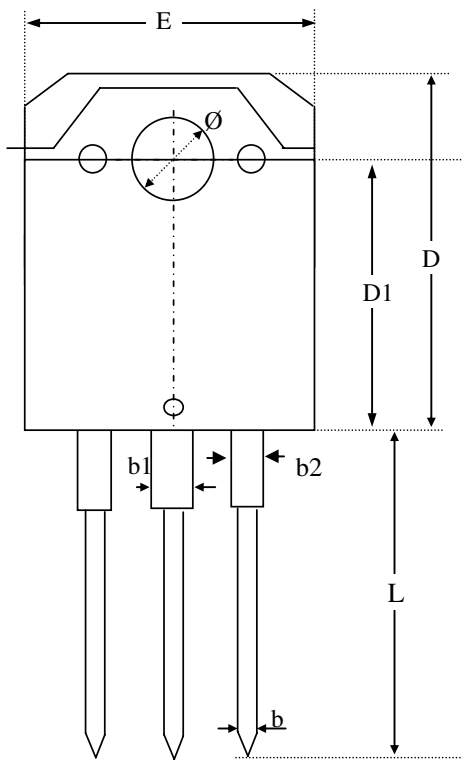


Fig 12. Gate Charge Characteristics

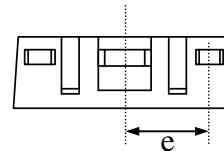


Package Dimensions: TO-3P



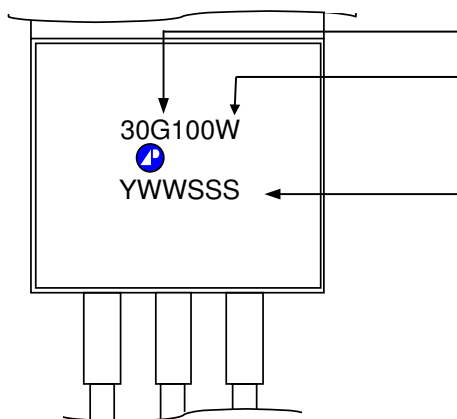
YMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.50	4.80	5.10
b	0.90	1.00	1.30
b1	1.80	2.50	3.20
b2	1.30	--	2.30
c	0.40	0.60	0.90
c1	1.40	--	2.20
D	19.70	20.00	20.30
D1	14.70	15.00	15.30
E	15.30	--	16.10
e	4.45	5.45	6.45
L	17.50	--	20.50
Ø	3.00	3.20	3.40

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.



Marking Information: TO-3P

Laser Marking



Product: AP30G100

Package code:

W = RoHS-compliant halogen-free TO-3P

Date/lot code (YWWSSS)

Y: Last digit of the year

WW: Work week

SSS: Lot code sequence